

CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV

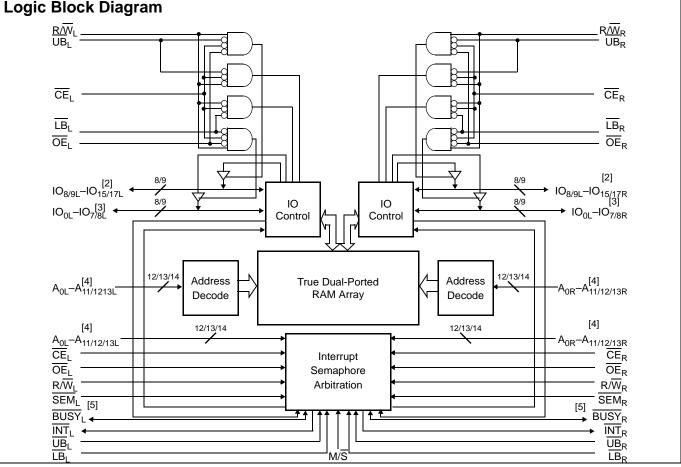
3.3V 4K/8K/16K x 16/18 Dual-Port Static RAM

Features

- True dual-ported memory cells which enable simultaneous access of the same memory location
- 4, 8 or 16K × 16 organization
- (CY7C024AV/024BV [1]/ 025AV/026AV)
- 4 or 8K × 18 organization (CY7C0241AV/0251AV)
- 16K × 18 organization (CY7C036AV)
- 0.35 micron CMOS for optimum speed and power
- High speed access: 20 and 25 ns
- Low operating power

□ Active: I_{CC} = 115 mA (typical) □ Standby: I_{SB3} = 10 μA (typical)

- Fully asynchronous operation
- Automatic power down
- Expandable data bus to 32 bits, 36 bits or more using Master and Slave chip select when using more than one device
- On chip arbitration logic
- Semaphores included to permit software handshaking between ports
- INT flag for port-to-port communication
- Separate upper byte and lower byte control
- Pin select for Master or Slave (M/S)
- Commercial and industrial temperature ranges
- Available in 100-pin Pb-free TQFP and 100-pin TQFP



Notes

- 1. CY7C024AV and CY7C024BV are functionally identical.
- 2. IO₈–IO₁₅ for x16 devices; IO₉–IO₁₇ for x18 devices.
- 3.
- $IO_0 IO_7$ for x16 devices; $IO_0 IO_8$ for x18 devices. <u>A_0 A_{11}</u> for 4K devices; A_0 A_{12} for 8K devices; A_0 A_{13} for 16K devices. 4.
- 5. BUSY is an output in master mode and an input in slave mode.

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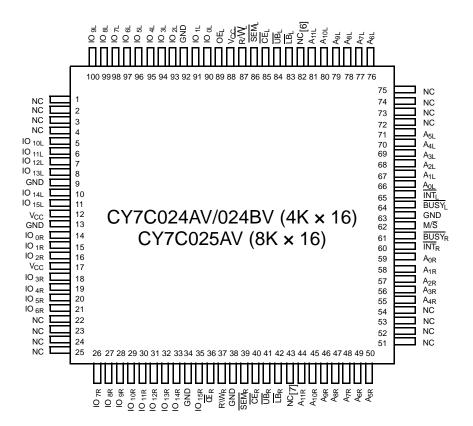
San Jose, CA 95134-1709

408-943-2600 ٠ Revised December 10, 2008



Pin Configurations

Figure 1. 100-Pin TQFP (Top View)



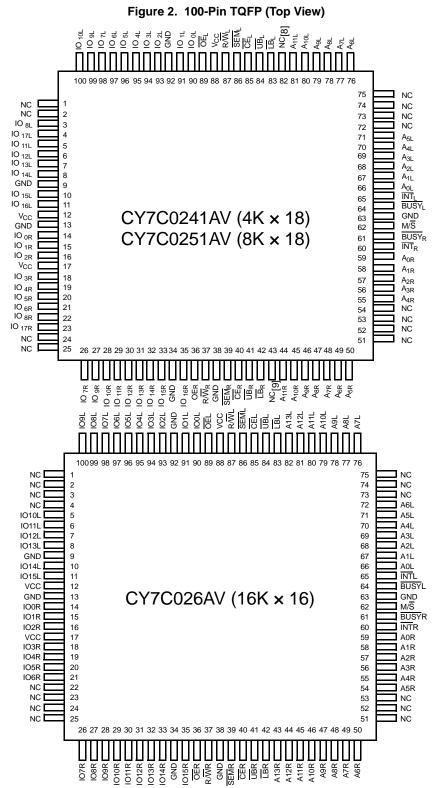
Notes

6. A_{12L} on the CY7C025AV. 7. A_{12R} on the CY7C025AV.

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Pin Configurations (continued)



Notes

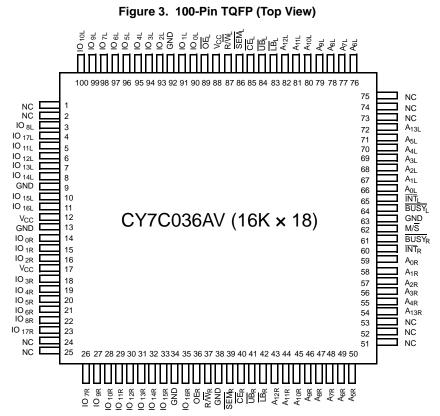
8. A_{12L} on the CY7C0251AV. 9. A_{12R} on the CY7C0251AVC.

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Pin Configurations (continued)



Selection Guide

Parameter	CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV -20	CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV -25	Unit
Maximum Access Time	20	25	ns
Typical Operating Current	120	115	mA
Typical Standby Current for I _{SB1} (Both ports TTL Level)	35	30	mA
Typical Standby Current for I _{SB3} (Both ports CMOS Level)	10	10	μA



Pin Definitions

Left Port	Right Port	Description
CEL	CER	Chip Enable
R/WL	R/WR	Read and Write Enable
OEL	OE _R	Output Enable
A _{0L} -A _{13L}	A _{0R} –A _{13R}	Address (A_0-A_{11} for 4K devices; A_0-A_{12} for 8K devices; A_0-A_{13} for 16K)
IO _{0L} –IO _{17L}	IO _{0R} –IO _{17R}	Data Bus Input and Output
SEML	SEMR	Semaphore Enable
UBL	UB _R	Upper Byte Select (IO_8 – IO_{15} for x16 devices; IO_9 – IO_{17} for x18 devices)
LBL	LB _R	Lower Byte Select ($IO_0 - IO_7$ for x16 devices; $IO_0 - IO_8$ for x18 devices)
INTL	INT _R	Interrupt Flag
BUSYL	BUSYR	Busy Flag
M/S		Master or Slave Select
V _{CC}		Power
GND		Ground
NC		No Connect

Architecture

CY7C024AV/024BV/025AV/026AV The and CY7C0241AV/0251AV/036AV consist of an array of 4K, 8K, and 16K words of 16 and 18 bits each of dual-port RAM cells, IO and address lines, and control signals (CE, OE, RW). These control pins permit independent access for reads or writes to any location in memory. To handle simultaneous writes and reads to the same location, a BUSY pin is provided on each port. Two Interrupt (INT) pins can be used for port to port communication. Two Semaphore (SEM)_control pins are used for allocating shared resources. With the M/S pin, the devices can function as a master (BUSY pins are outputs) or as a slave (BUSY pins are inputs). They also have an automatic power down feature controlled by CE. Each port has its own output enable control (OE), which enables data to be read from the device.

Functional Description

CY7C024AV/024BV/025AV/026AV The and CY7C0241AV/0251AV/036AV are low power CMOS 4K, 8K, and 16K ×16/18 dual port static RAMs. Various arbitration schemes are included on the devices to handle situations when multiple processors access the same piece of data. There are two ports permitting independent, asynchronous access for reads and writes to any location in memory. The devices can be used as standalone 16 or18-bit dual port static RAMs or multiple devices can be combined to function as a 32 or 36-bit or wider master and slave dual port static RAM. An M/\overline{S} pin is provided for implementing 32 or 36-bit or wider memory applications. It does not need separate master and slave devices or additional discrete logic. Application areas include interprocessor/multiprocessor designs, communications status buffering, and dual port video and graphics memory.

Each port has independent control pins: Chip Enable (\overline{CE}), Read or Write Enable (R/W), and Output Enable (\overline{OE}). Two flags are provided on each port (BUSY and INT). BUSY signals that the port is trying to access the same location currently being

accessed by the other port. The Interrupt flag ($\overline{\text{INT}}$) permits communication between ports or systems by means of a mail box. The semaphores are used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphore logic has eight shared latches. Only one side can control the latch (semaphore) at any time. Control of a semaphore indicates that a shared resource is in use. An automatic power down feat<u>ure</u> is controlled independently on each port by a Chip Select ($\overline{\text{CE}}$) pin.

TheCY7C024AV/024BV/025AV/026AVandCY7C0241AV0251AV/036AV are available in 100-pin Pb-free ThinQuad Flat Pack (TQFP) and 100-pin TQFP.

Write Operation

Data must be set up for a duration of t_{SD} before the rising edge of RW to guarantee a valid write. A write operation is controlled by either the RW pin (see Figure 8 on page 12) or the CE pin (see Figure 9 on page 12). Required inputs for non-contention operations are summarized in Table 1 on page 7.

If a location is being written to by one port and the opposite port tries to read that location, there must be a port to port flowthrough delay before the data is read on the output; otherwise the data read is not deterministic. Data is valid on the port t_{DDD} after the data is presented on the other port.

Read Operation

<u>When reading the device, the user must assert both the \overline{OE} and CE pins. Data is available t_{ACE} after CE or t_{DOE} after OE is asserted. If the user wants to access a semaphore flag, then the SEM pin and OE must be asserted.</u>

Interrupts

The upper two memory locations are for message passing. The highest memory location (FFF for the CY7C024AV/024BV/41AV/1FFF for the CY7C025AV/51AV,



3FFF for the CY7C026AV/36AV) is the mailbox for the right port and the second highest memory location (FFE for the CY7C024AV/024BV/41AV/1FFE for the CY7C025AV/51AV, 3FFE for the CY7C026AV/36AV) is the mailbox for the left port. When one port writes to the other port's mailbox, an interrupt is generated to the owner. The interrupt is reset when the owner reads the contents of the mailbox. The message is user defined.

Each port can read the other port's mailbox without resetting the interrupt. The active state of the busy signal (to a port) prevents the port from setting the interrupt to the winning port. Also, an active busy to a port prevents that port from reading its own mailbox and, thus, resetting the interrupt to it.

If an application does not require message passing, do not connect the interrupt pin to the processor's interrupt request input pin.

The operation of the interrupts and their interaction with Busy are summarized in Table 2 on page 7.

Busy

The CY7C024AV/024BV/025AV/026AV and CY7C0241AV/0251AV/036AV provide on-chip arbitration to resolve simultaneous memory location access (contention). If both ports' CEs are asserted and an address match occurs within t_{PS} of each other, the busy logic determines which port has access. If t_{PS} is violated, one port definitely gains permission to the location, but it is not predictable which port gets that permission. BUSY is asserted t_{BLA} after an address match or t_{BLC} after CE is taken LOW.

Master/Slave

A M/ \overline{S} pin helps to expand the word width by configuring the device as a master or a slave. The BUSY output of the master is connected to the BUSY input of the slave. This enables the device to interface to a master device with no external components. Writing to slave devices must be delayed until after the BUSY input has settled (t_{BLC} or t_{BLA}). Otherwise, the slave chip may begin a write cycle during a contention situation. When tied HIGH, the M/ \overline{S} pin enables the device to be used as a master and, therefore, the BUSY line is an output. BUSY can then be used to send the arbitration outcome to a slave.

Semaphore Operation

The CY7C024AV/024BV/025AV/026AV and CY7C0241AV/0251AV/036AV provide eight semaphore latches, which are separate from the dual port memory locations. Semaphores are used to reserve resources that are shared between the two ports. The state of the semaphore indicates that a resource is in use. For example, if the left port wants to request a given resource, it sets a latch by writing a zero to a semaphore location. The left port then verifies its success in setting the latch by reading it. After writing to the semaphore, SEM or OE must be deasserted for t_{SOP} before attempting to read the semaphore. The semaphore value is available $t_{SWRD} + t_{DOE}$ after the rising edge of the semaphore write. If the left port was successful (reads a zero), it assumes control of the shared resource. Otherwise (reads a one), it assumes the right port has control and continues to poll the semaphore. When the right side has relinquished control of the semaphore (by writing a one), the left side succeeds in gaining control of the semaphore. If the left side no longer requires the semaphore, a one is written to cancel its request.

Semaphores are accessed by asserting \overline{SEM} LOW. The \overline{SEM} pin functions as a chip select for the semaphore latches (\overline{CE} must remain HIGH <u>during</u> \overline{SEM} LOW). A₀₋₂ represents the semaphore address. \overline{OE} and RW are used in the same manner as a normal memory access. When writing or reading a semaphore, the other address pins have no effect.

When writing to the semaphore, only IO_0 is used. If a zero is written to the left port of an available semaphore, a one appears at the same semaphore address on the right port. That semaphore can now only be modified by the side showing zero (the left port in this case). If the left port now relinquishes control by writing a one to the semaphore, the semaphore is set to one for both sides. However, if the right port had requested the semaphore (written a zero) while the left port had control, the right port would immediately own the semaphore as soon as the left port released it. *Table 3* on page 7 shows sample semaphore operations.

When reading a semaphore, all 16 and 18 data lines output the semaphore value. The read value is latched in an output register to prevent the semaphore from changing state during a write from the other port. If both ports attempt to access the semaphore within t_{SPS} of each other, the semaphore is definitely obtained by one of them. But there is no guarantee which side controls the semaphore.



Table 1. Non-Contending Read/Write

	Inputs					Outputs		Orantian
CE	R/W	OE	UB	LB	SEM	10 ₉ –10 ₁₇	IO ₀ –IO ₈	Operation
Н	Х	Х	Х	Х	Н	High Z	High Z	Deselected: Power Down
Х	Х	Х	н	Н	Н	High Z	High Z	Deselected: Power Down
L	L	Х	L	Н	Н	Data In	High Z	Write to Upper Byte Only
L	L	Х	н	L	Н	High Z	Data In	Write to Lower Byte Only
L	L	Х	L	L	Н	Data In	Data In	Write to Both Bytes
L	Н	L	L	Н	Н	Data Out	High Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High Z	Data Out	Read Lower Byte Only
L	Н	L	L	L	Н	Data Out	Data Out	Read Both Bytes
Х	Х	Н	Х	Х	Х	High Z	High Z	Outputs Disabled
Н	Н	L	Х	Х	L	Data Out	Data Out	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	Data Out	Data Out	Read Data in Semaphore Flag
Н	2	Х	Х	Х	L	Data In	Data In	Write D _{IN0} into Semaphore Flag
Х		Х	Н	Н	L	Data In	Data In	Write D _{IN0} into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

Table 2. Interrupt Operation Example (assumes $\overline{\text{BUSY}}_{\text{L}} = \overline{\text{BUSY}}_{\text{R}} = \text{HIGH})^{[10]}$

		Left Port					Right Port					
Function	R/₩ _L	$R/W_L \overline{CE}_L \overline{OE}_L A_{0L-13L} \overline{INT}_L$		R/W _R	CER	OER	A _{0R-13R}	INT _R				
Set Right INT _R Flag	L	L	Х	FFF ^[13]	Х	Х	Х	Х	Х	L ^[12]		
Reset Right INT _R Flag	Х	Х	Х	Х	Х	Х	L	L	FFF (or 1/3FFF)	H ^[11]		
Set Left INT _L Flag	Х	Х	Х	Х	L ^[11]	L	L	Х	1FFE (or 1/3FFE)	Х		
Reset Left INT _L Flag	Х	L	L	1FFE ^[13]	H ^[12]	Х	Х	Х	Х	Х		

Table 3. Semaphore Operation Example

Function	IO ₀ -IO ₁₇ Left	IO ₀ -IO ₁₇ Right	Status
No action	1	1	Semaphore-free
Left port writes 0 to semaphore	0	1	Left Port has semaphore token
Right port writes 0 to semaphore	0	1	No change. Right side has no write access to semaphore
Left port writes 1 to semaphore	1	0	Right port obtains semaphore token
Left port writes 0 to semaphore	1	0	No change. Left port has no write access to semaphore
Right port writes 1 to semaphore	0	1	Left port obtains semaphore token
Left port writes 1 to semaphore	1	1	Semaphore-free
Right port writes 0 to semaphore	1	0	Right port has semaphore token
Right port writes 1 to semaphore	1	1	Semaphore free
Left port writes 0 to semaphore	0	1	Left port has semaphore token
Left port writes 1 to semaphore	1	1	Semaphore-free

Notes

10. See Functional Description on page 5 for specific highest memory locations by device. 11. If <u>BUSY</u>_R=L, then no change.

If BUSY_L=L, then no change.
 See Functional Description on page 5 for specific addresses by device.



Maximum Ratings

Exceeding maximum ratings^[14] may shorten the useful life of the device. User guidelines are not tested.

Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied55°C to +125°C
Supply Voltage to Ground Potential0.5V to +4.6V
DC Voltage Applied to Outputs in High-Z State0.5V to V _{CC} + 0.5V

Electrical Characteristics

Over the Operating Range

DC Input Voltage ^[15]	–0.5V to V _{CC} + 0.5V
Output Current into Outputs (LOW)	20 mA
Static Discharge Voltage	> 2001V
Latch-up Current	> 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	$3.3V\pm300~mV$
Industrial ^[16]	–40°C to +85°C	$3.3V\pm300~mV$

	Description			CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV						
Parameter				-20			Unit			
				Тур	Max	Min	Тур	Max		
V _{OH}	Output HIGH Voltage (V _{CC} =3.3V)					2.4			V	
V _{OL}	Output LOW Voltage				0.4			0.4	V	
V _{IH}	Input HIGH Voltage		2.0			2.0			V	
V _{IL}	Input LOW Voltage	Input LOW Voltage			0.8			0.8	V	
I _{OZ}	Output Leakage Current				10	-10		10	μΑ	
I _{IX}	Input Leakage Current		-10		10	-10		10	μΑ	
I _{CC}	Operating Current (V _{CC} = Max.,	Com'l.		120	175		115	165	mA	
	I _{OUT} = 0 mA) Outputs Disabled	Ind. ^[16]			•		135	185	mA	
I _{SB1}	Standby Current (Both Ports TTL Level)	Com'l.		35	45		30	40	mA	
	$CE_L \& CE_R \ge V_{IH}, f = f_{MAX}$	Ind. ^[16]					40	50	mA	
I _{SB2}	Standby Current (One Port TTL Level)	Com'l.		75	110		65	95	mA	
	$CE_L \mid CE_R \ge V_{IH}, f = f_{MAX}$	Ind. ^[16]					75	105	mA	
I _{SB3}	Standby Current (Both Ports CMOS Level)	Com'l.		10	500		10	500	μΑ	
	$CE_L \& CE_R \ge V_{CC} - 0.2V, f = 0$	Ind. ^[16]					10	500	μΑ	
I _{SB4}	$\frac{Standby Current (One Port CMOS Level)}{CE_L CE_R \ge V_{IH}, f = f_{MAX}^{[18]}}$	Com'l.	1	70	95		60	80	mA	
	$CE_L \mid CE_R \ge V_{IH}, f = f_{MAX}^{l \mid o_J}$	Ind. ^[16]	1				70	90	mA	

Capacitance

Parameter ^[19]	Description	Test Conditions	Max	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3V$	10	pF

Notes

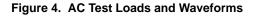
- 14. The voltage on any input or IO pin cannot exceed the power pin during power up.
- 15. Pulse width < 20 ns.
- 16. Industrial parts are available in CY7C026AV and CY7C036AV only.

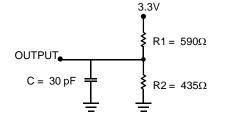
^{17.} VIL ≥ -1.5 V for pulse width less than 10ns. 18. f_{MAX} = 1/t_{RC} = All inputs cycling at f = 1/t_{RC} (except output enable). f = 0 means no address or control lines change. This applies only to inputs at CMOS level standby I_{SB3}.

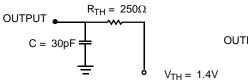
^{19.} Tested initially and after any design or process changes that may affect these parameters.

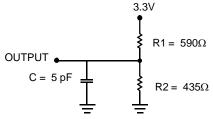


CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV







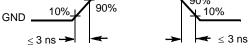


(c) Three-State Delay (Load 2) (Used for t_{LZ} , t_{HZ} , t_{HZWE} , and t_{LZWE} including scope and jig)

(a) Normal Load (Load 1)



(b) Thévenin Equivalent (Load 1)



Switching Characteristics

Over the Operating Range [20]

		CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV					
Description	-	20	-:	Unit			
	Min	Max	Min	Max			
Read Cycle Time	20		25		ns		
Address to Data Valid		20		25	ns		
Output Hold From Address Change	3		3		ns		
CE LOW to Data Valid		20		25	ns		
OE LOW to Data Valid		12		13	ns		
OE Low to Low Z	3		3		ns		
OE HIGH to High Z		12		15	ns		
CE LOW to Low Z	3		3		ns		
CE HIGH to High Z		12		15	ns		
CE LOW to Power Up	0		0		ns		
CE HIGH to Power Down		20		25	ns		
Byte Enable Access Time		20		25	ns		
	L. L		1				
Write Cycle Time	20		25		ns		
CE LOW to Write End	15		20		ns		
Address Valid to Write End	15		20		ns		
Address Hold From Write End	0		0		ns		
Address Setup to Write Start	0		0		ns		
	Address to Data Valid Output Hold From Address Change CE LOW to Data Valid OE LOW to Data Valid OE LOW to Low Z OE HIGH to High Z CE LOW to Low Z CE HIGH to High Z CE LOW to Power Up CE HIGH to Power Down Byte Enable Access Time Write Cycle Time CE LOW to Write End Address Valid to Write End Address Hold From Write End	Description CY Min Min Read Cycle Time 20 Address to Data Valid 20 Output Hold From Address Change 3 CE LOW to Data Valid 3 OE LOW to Data Valid 3 OE LOW to Data Valid 3 OE Low to Low Z 3 CE LOW to Low Z 3 CE LOW to Date Valid 0 OE HIGH to High Z 3 CE LOW to Low Z 3 CE LOW to Power Up 0 CE LOW to Power Up 0 CE HIGH to Power Down 9 Byte Enable Access Time 20 Vrite Cycle Time 20 CE LOW to Write End 15 Address Valid to Write End 15 Address Hold From Write End 0	CYTC0241 AV/ -20DescriptionCYTC0241 AV/Read Cycle TimeMaxRead Cycle Time20Address to Data Valid20Output Hold From Address Change3CE LOW to Data Valid20OE LOW to Data Valid12OE LOW to Data Valid12OE LOW to Data Valid12OE LOW to Low Z3CE LOW to Low Z3CE HIGH to High Z12CE LOW to Power Up0CE HIGH to Power Up0CE HIGH to Power Down20Byte Enable Access Time20Write Cycle Time20CE LOW to Write End15Address Valid to Write End15Address Hold From Write End0	CYTC0241AV/0251AV/030DescriptionRead Cycle Time2025Address to Data Valid2025Address to Data Valid2020Output Hold From Address Change33CE LOW to Data Valid2020OE LOW to Data Valid2020OE LOW to Data Valid12OE Low to Low Z33CE LOW to Low Z33CE HIGH to High Z12CE LOW to Power Up00CE HIGH to Power Down20Byte Enable Access Time20Write Cycle Time20Write Cycle Time20CE LOW to Write End15Address Valid to Write End000Address Hold From Write End000Address Hold From Write End00000	DescriptionCY7C0241AV/0251AV/036AVImage: Partial colspan="2">-20-25MinMaxMinMaxRead Cycle Time202525Address to Data Valid202525Output Hold From Address Change333CE LOW to Data Valid202525OE LOW to Data Valid12133OE Low to Low Z333OE HIGH to High Z121515CE LOW to Dower Up000CE HIGH to High Z121525DE Low to Power Up0025Byte Enable Access Time2025Write Cycle Time2025CE LOW to Write End1520Address Valid to Write End1520Address Hold From Write End00		

Notes

20. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified $I_{O/}I_{OH}$ and 30 pF load capacitance. 21. To access RAM, $\overrightarrow{CE} = L$, $\overrightarrow{UB} = L$, $\overrightarrow{SEM} = H$. To access semaphore, $\overrightarrow{CE} = H$ and $\overrightarrow{SEM} = L$. Either condition must be valid for the entire t_{SCE} time.

22. At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZOE} is less than t_{LZOE} .

23. Test conditions used are Load 3.

24. This parameter is guaranteed but not tested. For information on port to port delay through RAM cells from writing port to reading port, refer to Figure 12.



Switching Characteristics

Over the Operating Range (continued)^[20]

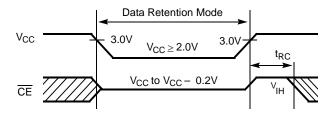
ParameterDescription -20 -2 MinMaxMin t_{PWE} Write Pulse Width1520 t_{SD} Data Setup to Write End1515 t_{HD} Data Hold From Write End00 $t_{HZWE}^{[23, 24]}$ R/W LOW to High Z12 $t_{LZWE}^{[23, 24]}$ R/W HIGH to Low Z30 $t_{WDD}^{[25]}$ Write Pulse to Data Delay45 $t_{DDD}^{[25]}$ Write Data Valid to Read Data Valid30Busy Timing ^[26] t_{BLA} BUSY LOW from Address Match20	CY7C024AV/024BV/025AV/026AV CY7C0241AV/0251AV/036AV					
t _{PWE} Write Pulse Width 15 20 t _{SD} Data Setup to Write End 15 15 t _{HD} Data Hold From Write End 0 0 t _{HZWE} ^[23, 24] R/W LOW to High Z 12 12 t _{LZWE} ^[23, 24] R/W HIGH to Low Z 3 0 t _{LZWE} ^[23, 24] Write Pulse to Data Delay 45 12 t _{DDD} ^[25] Write Data Valid to Read Data Valid 30 30	-25					
$\begin{tabular}{ c c c c c c } \hline FWL & & & & & & & & & & & & & & & & & & &$	Max					
$\begin{array}{c c c c c c c c c } \hline t_{HD} & Data Hold From Write End & 0 & 0 \\ \hline t_{HZWE}^{[23,24]} & R/\overline{W} LOW to High Z & 12 \\ \hline t_{LZWE}^{[23,24]} & R/\overline{W} HIGH to Low Z & 3 & 0 \\ \hline t_{WDD}^{[25]} & Write Pulse to Data Delay & 45 \\ \hline t_{DDD}^{[25]} & Write Data Valid to Read Data Valid & 30 \\ \hline \textbf{Busy Timing}^{[26]} \end{array}$		ns				
Ind R/W LOW to High Z 12 t _{HZWE} R/W LOW to High Z 12 t _{LZWE} R/W HIGH to Low Z 3 0 t _{WDD} R/W HIGH to Low Z 3 0 t _{WDD} Write Pulse to Data Delay 45 12 t _{DDD} Write Data Valid to Read Data Valid 30 30		ns				
t_LZWE [23, 24] R/W HIGH to Low Z 3 0 t _{WDD} Write Pulse to Data Delay 45 0 t _{DDD} Write Data Valid to Read Data Valid 30 30 Busy Timing 26 0 0		ns				
t_LZWE [23, 24] R/W HIGH to Low Z 3 0 t _{WDD} Write Pulse to Data Delay 45 0 t _{WDD} Write Data Valid to Read Data Valid 30 30 Busy Timing [26] Image: Comparison of the pulse of t	15	ns				
t _{WDD} ^[25] Write Pulse to Data Delay 45 t _{DDD} ^[25] Write Data Valid to Read Data Valid 30		ns				
t _{DDD} ^[25] Write Data Valid to Read Data Valid 30 Busy Timing ^[26]	50	ns				
	35	ns				
t _{BLA} BUSY LOW from Address Match 20		<u> </u>				
	20	ns				
t _{BHA} BUSY HIGH from Address Mismatch 20	20	ns				
t _{BLC} BUSY LOW from CE LOW 20	20	ns				
t _{BHC} BUSY HIGH from CE HIGH 17	17	ns				
t _{PS} Port Setup for Priority 5 5		ns				
t _{WB} R/W HIGH after BUSY (Slave) 0 0		ns				
t _{WH} R/W HIGH after BUSY HIGH (Slave) 15 17		ns				
t _{BDD} ^[27] BUSY HIGH to Data Valid 20	25	ns				
Interrupt Timing ^[26]		<u> </u>				
t _{INS} INT Set Time 20	20	ns				
t _{INR} INT Reset Time 20	20	ns				
Semaphore Timing		-				
t _{SOP} SEM Flag Update Pulse (OE or SEM) 10 12		ns				
t _{SWRD} SEM Flag Write to Read Time 5 5		ns				
t _{SPS} SEM Flag Contention Window 5 5		ns				
t _{SAA} SEM Address Access Time 20	25	ns				

Data Retention Mode

CY7C024AV/024BV/025AV/026AV The and CY7C0241AV/0251AV/036AV are designed for battery backup. Data retention voltage and supply current are guaranteed over temperature. The following rules ensure data retention:

- 1. Chip Enable (\overline{CE}) must be held HIGH during data retention, within V_{CC} to $V_{CC} - 0.2V$.
- 2. \overline{CE} must be kept between V_{CC} 0.2V and 70 percent of V_{CC} during the power up and power down transitions.
- 3. The RAM can begin operation $> t_{RC}$ after V_{CC} reaches the minimum operating voltage (3.0V).

Timing



Parameter	Test Conditions ^[28]	Max	Unit
ICC _{DR1}	at VCC _{DR} = 2V	50	μA

Notes

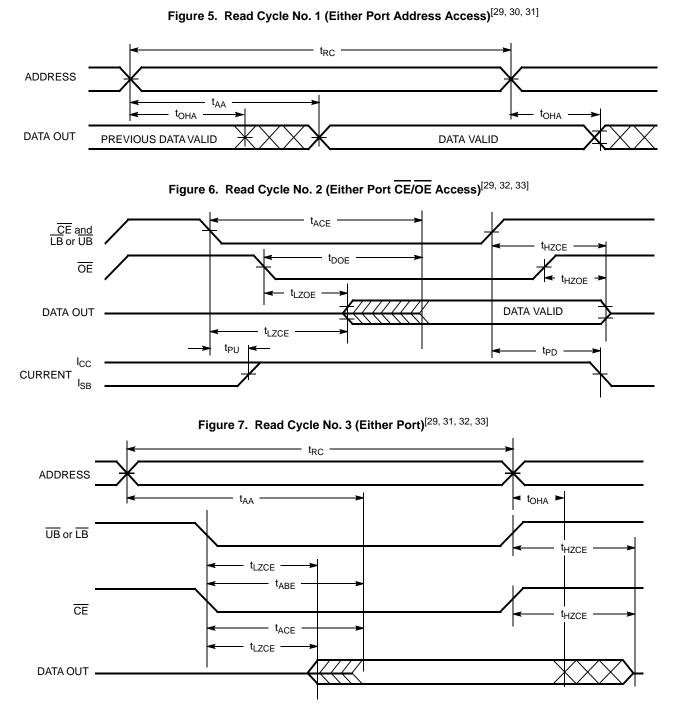
25. For information on port to port delay through RAM cells from writing port to reading port, refer to Figure 12.

26. Test conditions used are Load 2.

27. <u>t_{RDD}</u> is a calculated parameter and is the greater of t_{WDD} – t_{PWE} (actual) or t_{DDD} – t_{SD} (actual). 28. CE = V_{CC}, V_{in} = GND to V_{CC}, T_A = 25°C. This parameter is guaranteed but not tested.



Switching Waveforms



Notes

29. R/ $\overline{\rm W}$ is HIGH for read cycles.

30. Device is continuously selected $\overline{CE} = V_{IL}$ and \overline{UB} or $\overline{LB} = V_{IL}$. This waveform cannot be used for semaphore reads. 31. $\overline{CE} = V_{IL}$.

32. Address valid prior to or coincident with \overline{CE} transition LOW. 33. To access RAM, $\overline{CE} = V_{IL}$, \overline{UB} or $\overline{LB} = V_{IL}$, $\overline{SEM} = V_{IH}$. To access semaphore, $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$.



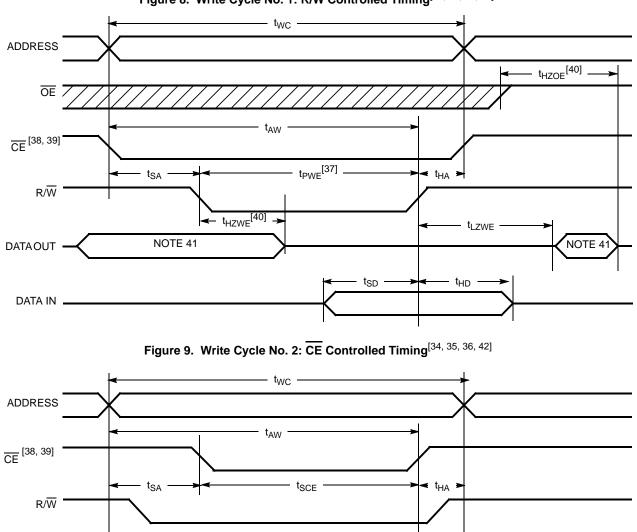


Figure 8. Write Cycle No. 1: R/W Controlled Timing^[34, 35, 36, 37]

Notes

DATA IN

- 34. R/W or CE must be HIGH during all address transitions.
- A white occurs during the overlap (t_{SCE} or t_{PWE}) of a LOW CE or SEM and a LOW UB or LB.
 t_{Ha} is measured from the <u>e</u>arlier of CE or RW or (SEM or R/W) going HIGH at the end of write cycle.
- 33. If OE is LOW during a R/W controlled write cycle, the write pulse width must be the larger of t_{PWE} or (t_{HZWE} + t_{SD}) to enable the IO drivers to turn off and data to be placed on the bus for the required t_{SD}. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t<u>pWE</u>.
 38. To access RAM, CE = V_{IL}, SEM = V_{IH}.
 39. To access lower byte, CE = V_{IL}, JB = V_{IL}, SEM = V_{IH}.
 40. Transition is measured ±500 mV from steady state with a 5 pF load (including scope and jig). This parameter is sampled and not 100 percent tested.

tsp

t_{HD}

- 41. During this period, the IO pins are in the output state, and input signals must not be applied.
- 42. If the CE or SEM LOW transition occurs simultaneously with or after the RIW LOW transition, the outputs remain in the high impedance state.



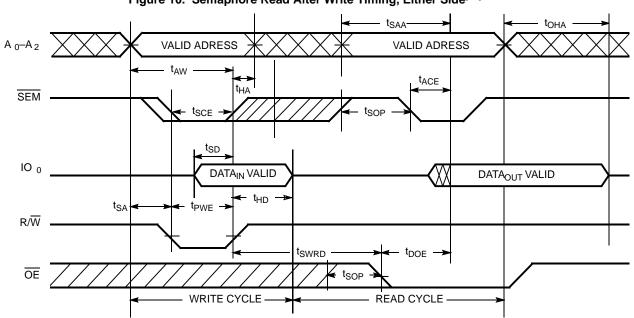
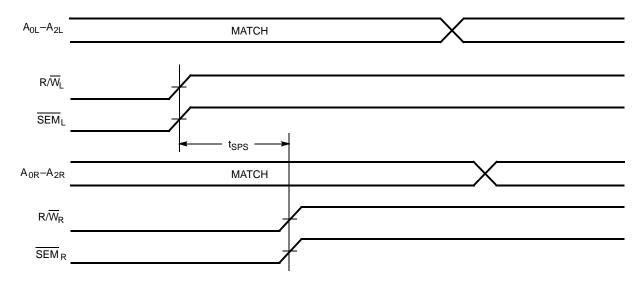


Figure 10. Semaphore Read After Write Timing, Either Side^[43]

Figure 11. Timing Diagram of Semaphore Contention^[44, 45, 46]



Notes 43. \overline{CE} = HIGH for the duration of the above timing (both write and read cycle). 44. IO_{0R} = IO_{0L} = LOW (request semaphore); \overline{CE}_R = \overline{CE}_L = HIGH. 45. Semaphores are reset (available to both ports) at cycle start. 46. If t_{SPS} is violated, the semaphore is definitely obtained by one side or the other, but which side gets the semaphore is unpredictable.



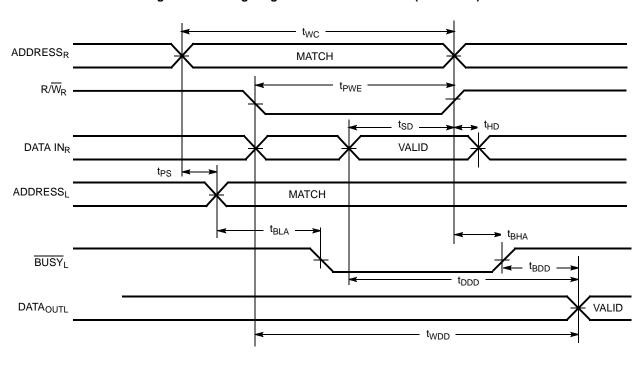
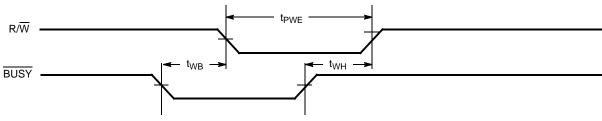


Figure 12. Timing Diagram of Read with $\overline{\text{BUSY}}$ (M/S=HIGH)^[47]

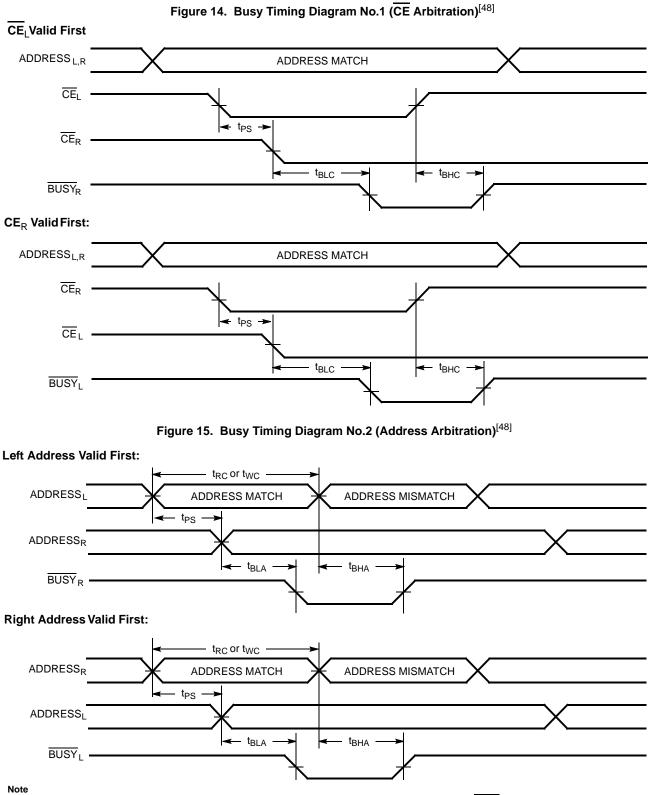




$$\frac{\text{Note}}{47. \text{ CE}_{\text{L}}} = \overline{\text{CE}}_{\text{R}} = \text{LOW}.$$

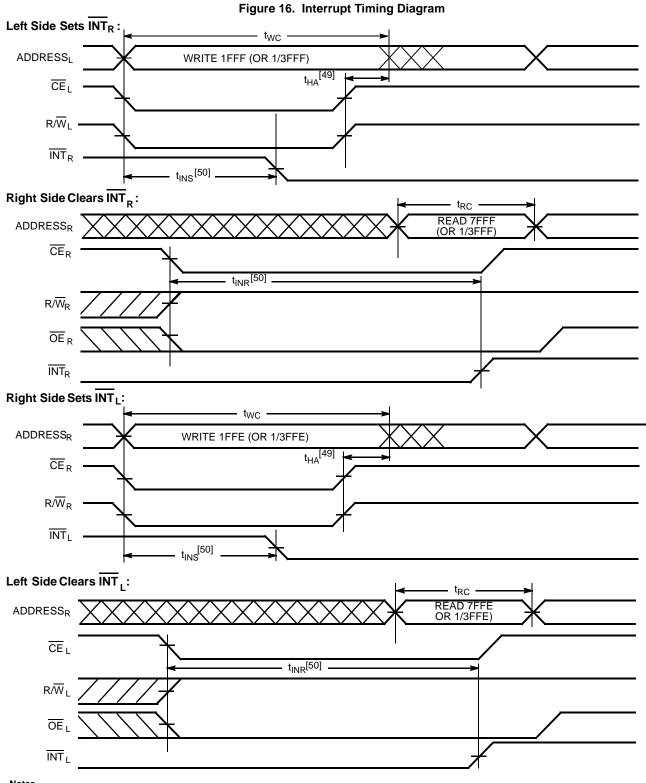
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48. If t_{PS} is violated, the busy signal is asserted on one side or the other, but there is no guarantee to which side BUSY is asserted.





Notes

49. t_{HA} depends on which enable pin (\overline{CE}_L or $\underline{R}/\overline{W}_L$) is deasserted first. 50. t_{INS} or t_{INR} depends on which enable pin (\overline{CE}_L or $\overline{R}/\overline{W}_L$) is asserted last.



Ordering Information

4K x16 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C024AV-15AI 51-85048 100-Pin Thin Quad Flat Pack		100-Pin Thin Quad Flat Pack	Industrial
	CY7C024BV-15AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	
20	CY7C024AV-20AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial
	CY7C024AV-20AXC 51-85048 100-Pin Pb-Free Thin Quad Flat Pack			
	CY7C024AV-20AI	7C024AV-20AI 51-85048 100-Pin Thin Quad Flat Pack		Industrial
	CY7C024AV-20AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	
25	25 CY7C024AV-25AC 51-85048 100-Pin Thin Quad Flat Pack		100-Pin Thin Quad Flat Pack	Commercial
CY7C024AV-25AXC 51-85048 100-Pin Pl		100-Pin Pb-Free Thin Quad Flat Pack		
	CY7C024AV-25AI	51-85048	100-Pin Thin Quad Flat Pack	Industrial
	CY7C024AV-25AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	

8K x16 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C025AV-20AC	51-85048 100-Pin Thin Quad Flat Pack		Commercial
	CY7C025AV-20AXC	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	
	CY7C025AV-20AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	Industrial
25	Y7C025AV-25AC 51-85048 100-Pin Thin Quad Flat Pack		Commercial	
	CY7C025AV-25AXC	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	
	CY7C025AV-25AI	51-85048	100-Pin Thin Quad Flat Pack	Industrial
	CY7C025AV-25AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	

16K x16 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range	
20	CY7C026AV-20AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial	
	CY7C026AV-20AXC	51-85048	100-Pin Pb-Free Thin Quad Flat Pack		
	CY7C026AV-20AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack	Industrial	
25	CY7C026AV-25AC	51-85048 100-Pin Thin Quad Flat Pack		Commercial	
	CY7C026AV-25AXC	51-85048	100-Pin Pb-Free Thin Quad Flat Pack		
	CY7C026AV-25AI	51-85048	100-Pin Thin Quad Flat Pack	Industrial	
	CY7C026AV-25AXI	51-85048	100-Pin Pb-Free Thin Quad Flat Pack		

4K x18 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C0241AV-20AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial
25	CY7C0241AV-25AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial

8K x18 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C0251AV-20AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial
25	CY7C0251AV-25AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial

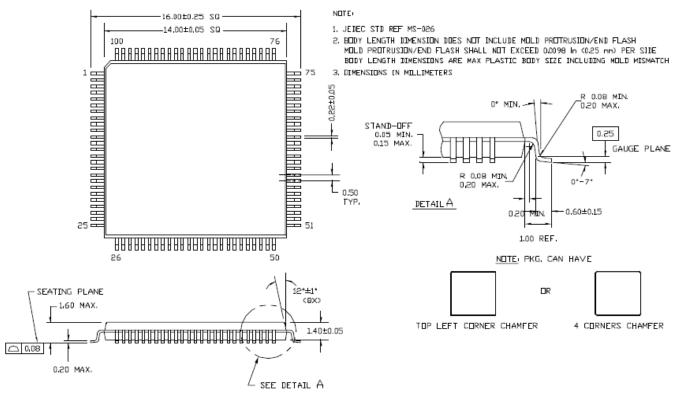


16K x18 3.3V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C036AV-20AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial
25	CY7C036AV-25AC	51-85048	100-Pin Thin Quad Flat Pack	Commercial
	CY7C036AV-25AXC	51-85048	100-Pin Pb-free Thin Quad Flat Pack	
	CY7C036AV-25AI	51-85048	100-Pin Thin Quad Flat Pack	Industrial

Package Diagram





51-85048 *C



Document History Page

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	110204	SZV	11/11/01	Change from Spec number: 38-00838 to 38-06052
*A	122302	RBI	12/27/02	Power up requirements added to Maximum Ratings Information
*В	128958	JFU	9/03/03	Added CY7C025AV-25AI to Ordering Information
*C	237622	YDT	See ECN	Removed cross information from features section
*D	241968	WWZ	See ECN	Added CY7C024AV-25AI to Ordering Information
*E	276451	SPN	See ECN	Corrected x18 for 026AV to x16
*F	279452	RUY	See ECN	Added Pb-free packaging information Corrected pin A113L to A13L on CY7C026AV pin list Added minimum V _{IL} of 0.3V and note 16
*G	373580	RUY	See ECN	Corrected CY7C024AC-25AXC to CY7C024AV-25AXC in Ordering Informatic
*H	380476	PCX	See ECN	Added to Part Ordering information: CY7C024AV-15AI, CY7C024AV-15AXI, CY7C024AV-20AI, CY7C024AV-20AXI, CY7C025AV-20AXI, CY7C026AV-20AXI
*	2543577	NXR/AESA	07/25/08	Updated note number 33 on page 12 from "R/W must be HIGH during all address transitions" to "R/W or CE must be HIGH during all address transition
*J	2623540	VKN/PYRS	12/17/08	Added CY7C024BV part

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